# 50 mA Ultra-Low Iq, Wide Input Voltage, Low Dropout Linear Voltage Regulator

The NCP715 is 50 mA LDO Linear Voltage Regulator. It is a very stable and accurate device with ultra–low ground current consumption (4.7  $\mu$ A over the full output load range) and a wide input voltage range (up to 24 V). The regulator incorporates several protection features such as Thermal Shutdown and Current Limiting.

### Features

- Operating Input Voltage Range: 2.5 V to 24 V
- Fixed Voltage Options Available: 1.2 V to 5.3 V
- Ultra Low Quiescent Current: Max. 4.7 µA Over Full Load and Temperature
- ±2% Accuracy Over Full Load, Line and Temperature Variations
- PSRR: 52 dB at 100 kHz
- Noise: 190  $\mu$ V<sub>RMS</sub> from 200 Hz to 100 kHz
- Thermal Shutdown and Current Limit protection
- Available in XDFN6 1.5 x 1.5 mm and SC-70 (SC-88A) Package
- These are Pb–Free Devices

### **Typical Applications**

- Portable Equipment
- Communication Systems

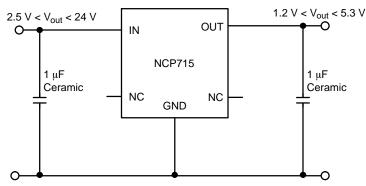
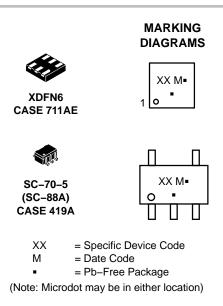


Figure 1. Typical Application Schematic



# **ON Semiconductor®**

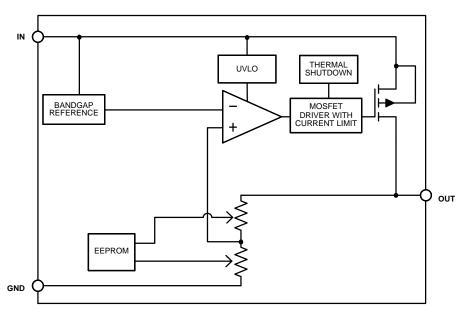
www.onsemi.com



#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 18 of this data sheet.

1





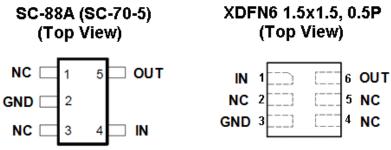


Figure 3. Pin Description

### PIN FUNCTION DESCRIPTION

Pin	No.		
SC-70	XDFN6	Pin Name	Description
5	6	OUT	Regulated output voltage pin. A small 0.47 $\mu F$ ceramic capacitor is needed from this pin to ground to assure stability.
1	2	N/C	No connection. This pin can be tied to ground to improve thermal dissipation or left disconnected.
2	3	GND	Power supply ground.
3	4	N/C	No connection. This pin can be tied to ground to improve thermal dissipation or left disconnected.
-	5	N/C	No connection. This pin can be tied to ground to improve thermal dissipation or left disconnected.
4	1	IN	Input pin. A small capacitor is needed from this pin to ground to assure stability.

### **ABSOLUTE MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Input Voltage (Note 1)	V <sub>IN</sub>	-0.3 to 24	V
Output Voltage	V <sub>OUT</sub>	-0.3 to 6	V
Output Short Circuit Duration	t <sub>SC</sub>	Indefinite	s
Maximum Junction Temperature	T <sub>J(MAX)</sub>	150	°C
Operating Ambient Temperature Range	T <sub>A</sub>	-40 to 125	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to 150	°C
ESD Capability, Human Body Model (Note 2)	ESD <sub>HBM</sub>	2000	V
ESD Capability, Machine Model (Note 2)	ESD <sub>MM</sub>	200	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.
This device series incorporates ESD protection and is tested by the following methods: ESD Human Body Model tested per EIA/JESD22-A114 ESD Machine Model tested per EIA/JESD22-A115 ESD Charged Device Model tested per EIA/JESD22-C101E
Lator un Currant Maximum Patina tested aper EIA/JESD22 - C101E

Latch up Current Maximum Rating tested per JEDEC standard: JESD78.

### THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Characteristics, SC–70 Thermal Resistance, Junction–to–Air	$R_{\thetaJA}$	390	°C/W
Thermal Characteristics, XDFN6 Thermal Resistance, Junction-to-Air	$R_{\thetaJA}$	260	°C/W

#### ELECTRICAL CHARACTERISTICS – Voltage Version 1.2 V

 $-40^{\circ}C \le T_J \le 125^{\circ}C$ ;  $V_{IN} = 2.5 \text{ V}$ ;  $I_{OUT} = 1 \text{ mA}$ ,  $C_{IN} = C_{OUT} = 1.0 \text{ }\mu\text{F}$ , unless otherwise noted. Typical values are at  $T_J = +25^{\circ}C$ . (Note 5)

Parameter	Test Conditions		Symbol	Min	Тур	Max	Unit
Operating Input Voltage	I <sub>OUT</sub> ≤ 10 mA		V <sub>IN</sub>	2.5		24	V
	10 mA< I <sub>OUT</sub> < 50 m	A		3.0		24	
Output Voltage Accuracy	2.5 V < V <sub>IN</sub> < 24 V, 0 < I <sub>OUT</sub>	≤ 10 mA	V <sub>OUT</sub>	1.164	1.2	1.236	V
	3.0 V < V <sub>IN</sub> < 24 V, 0 mA < I <sub>OL</sub>	<sub>JT</sub> < 50 mA	V <sub>OUT</sub>	1.164	1.2	1.236	V
	3.0 V < V <sub>IN</sub> < 24 V, 1 mA < I <sub>OU</sub> -20°C < T <sub>J</sub> < 125°C		V <sub>OUT</sub>	1.176	1.2	1.224	V
Line Regulation	$2.5 \text{ V} \leq \text{V}_{\text{IN}} \leq 24 \text{ V}, \text{ I}_{\text{OUT}} =$	: 1 mA	Reg <sub>LINE</sub>		2		mV
Load Regulation	I <sub>OUT</sub> = 0 mA to 50 m.	A	Reg <sub>LOAD</sub>		5		mV
Dropout Voltage (Note 3)			V <sub>DO</sub>			-	mV
Maximum Output Current	(Note 6)		I <sub>OUT</sub>	100		200	mA
	0 < I <sub>OUT</sub> < 50 mA, -40 < T <sub>A</sub>	, < 85°C	I <sub>GND</sub>		3.2	4.2	μΑ
	0 < I <sub>OUT</sub> < 50 mA, V <sub>IN</sub> =	24 V				5.8	
Power Supply Rejection Ratio		f = 100 kHz	PSRR		60		dB
Output Noise Voltage	V <sub>OUT</sub> = 1.2 V, I <sub>OUT</sub> = 50 f = 200 Hz to 100 kHz, C <sub>OUT</sub>	) mA <sub>Γ</sub> = 10 μF	V <sub>N</sub>		65		μV <sub>rms</sub>
Thermal Shutdown Temperature (Note 4)	Temperature increasing from	Г <sub>Ј</sub> = +25°С	T <sub>SD</sub>		170		°C
Thermal Shutdown Hysteresis (Note 4)	Temperature falling from	T <sub>SD</sub>	T <sub>SDH</sub>	-	15	-	°C

Not Characterized at V<sub>IN</sub> = 3.0 V, V<sub>OUT</sub> = 1.2 V, I<sub>OUT</sub> = 50 mA.
 Guaranteed by design and characterization.
 Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at T<sub>J</sub> = T<sub>A</sub> = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

6. Respect SOA.

#### ELECTRICAL CHARACTERISTICS – Voltage Version 1.5 V

 $-40^{\circ}C \le T_J \le 125^{\circ}C$ ;  $V_{IN} = 2.5 \text{ V}$ ;  $I_{OUT} = 1 \text{ mA}$ ,  $C_{IN} = C_{OUT} = 1.0 \text{ }\mu\text{F}$ , unless otherwise noted. Typical values are at  $T_J = +25^{\circ}C$ . (Note 9)

Parameter	Test Conditions	Symbol	Min	Тур	Max	Unit
Operating Input Voltage	I <sub>OUT</sub> ≤ 10 mA	V <sub>IN</sub>	2.5		24	V
	10 mA < I <sub>OUT</sub> < 50 mA		3.0		24	1
Output Voltage Accuracy	$2.5 \text{ V} < \text{Vin} < 24 \text{ V}, 0 < \text{I}_{\text{OUT}} \le 10 \text{ mA}$	V <sub>OUT</sub>	1.455	1.5	1.545	V
	3.0 V < VIN < 24 V, 0 < I <sub>OUT</sub> < 50 mA	V <sub>OUT</sub>	1.455	1.5	1.545	V
	$3.0 \text{ V} < \text{V}_{\text{IN}} < 24 \text{ V}, 1 \text{ mA} < \text{I}_{\text{OUT}} < 50 \text{ mA} -20^{\circ}\text{C} < \text{T}_{\text{J}} < 125^{\circ}\text{C};$	, V <sub>OUT</sub>	1.470	1.5	1.530	V
Line Regulation	Vout + 1 V $\leq$ VIN $\leq$ 24 V, I <sub>OUT</sub> = 1 mA	Reg <sub>LINE</sub>		2		mV
Load Regulation	I <sub>OUT</sub> = 0 mA to 50 mA	Reg <sub>LOAD</sub>		5		mV
Dropout Voltage (Note 7)		V <sub>DO</sub>			-	mV
Maximum Output Current	(Note 10)	IOUT	100		200	mA
Ground Current	0 < I <sub>OUT</sub> < 50 mA, -40 < T <sub>A</sub> < 85°C	I <sub>GND</sub>		3.2	4.2	μΑ
	0 < I <sub>OUT</sub> < 50 mA, V <sub>IN</sub> = 24 V				5.8	μΑ
Power Supply Rejection Ratio	$ \begin{array}{l} V_{IN}=3.0 \text{ V}, V_{OUT}=1.5 \text{ V} \\ V_{PP}=200 \text{ mV modulation} \\ I_{OUT}=1 \text{ mA}, C_{OUT}=10 \ \mu\text{F} \end{array} \right  f=100 \ \text{kH} \\ \end{array} $	z PSRR		56		dB
Output Noise Voltage	$V_{OUT}$ = 1.5 V, $I_{OUT}$ = 50 mA f = 200 Hz to 100 kHz, $C_{OUT}$ = 10 $\mu F$	V <sub>N</sub>		75		μV <sub>rms</sub>
Thermal Shutdown Temperature (Note 8)	Temperature increasing from $T_J = +25^{\circ}C$	; T <sub>SD</sub>		170		°C
Thermal Shutdown Hysteresis (Note 8)	Temperature falling from T <sub>SD</sub>	T <sub>SDH</sub>	-	15	-	°C

Not Characterized at V<sub>IN</sub> = 3.0 V, V<sub>OUT</sub> = 1.5 V, I<sub>OUT</sub> = 50 mA.
 Guaranteed by design and characterization.
 Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at T<sub>J</sub> = T<sub>A</sub> = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.
 Respect SOA.

### ELECTRICAL CHARACTERISTICS – Voltage Version 1.8 V

 $-40^{\circ}C \le T_J \le 125^{\circ}C$ ;  $V_{IN} = 2.8V$ ;  $I_{OUT} = 1 \text{ mA}$ ,  $C_{IN} = C_{OUT} = 1.0 \mu$ F, unless otherwise noted. Typical values are at  $T_J = +25^{\circ}C$ . (Note 13)

Parameter	Test Conditions	Symbol	Min	Тур	Max	Unit
Operating Input Voltage	Iouт ≤10 mA	V <sub>IN</sub>	2.8		24	V
	10 mA < I <sub>OUT</sub> < 50 mA		3.0		24	
Output Voltage Accuracy	2.8 V < V <sub>IN</sub> < 24 V, 0 < I <sub>OUT</sub> < 10 mA	V <sub>OUT</sub>	1.746	1.8	1.854	V
	$3.0 \text{ V} < \text{V}_{\text{IN}} < 24 \text{ V}, 1 \text{ mA} < \text{I}_{\text{OUT}} < 50 \text{ m}.$ $-20^{\circ}\text{C} < \text{T}_{\text{J}} < 125^{\circ}\text{C};$	A, V <sub>OUT</sub>	1.764	1.8	1.836	V
Line Regulation	$3 \text{ V} \leq \text{Vin} \leq 24 \text{ V}, \text{ I}_{OUT} = 1 \text{ mA}$	Reg <sub>LINE</sub>		3		mV
Load Regulation	I <sub>OUT</sub> = 0 mA to 50 mA	Reg <sub>LOAD</sub>		10		mV
Dropout Voltage (Note 11)		V <sub>DO</sub>				mV
Maximum Output Current	(Note 14)	I <sub>OUT</sub>	100		200	mA
Ground Current	0 < I <sub>OUT</sub> < 50 mA, −40 < T <sub>A</sub> < 85°C	I <sub>GND</sub>		3.2	4.2	μΑ
	0 < I <sub>OUT</sub> < 50 mA, V <sub>IN</sub> = 24 V				5.8	μΑ
Power Supply Rejection Ratio	$ \begin{array}{c} V_{IN} = 3.0 \text{ V}, \ V_{OUT} = 1.8 \text{ V} \\ V_{PP} = 200 \text{ mV modulation} \\ I_{OUT} = 1 \text{ mA}, \ C_{OUT} = 10 \ \mu\text{F} \end{array} \right  f = 100 \text{ kH} $	Hz PSRR		60		dB
Output Noise Voltage	Vout = 1.8 V, lout = 50 mA f = 200 Hz to 100 kHz, $C_{OUT}$ = 10 $\mu$ F	V <sub>N</sub>		95		$\mu V_{rms}$
Thermal Shutdown Temperature (Note 12)	Temperature increasing from $T_J = +25^{\circ}$	C T <sub>SD</sub>		170		°C
Thermal Shutdown Hysteresis (Note 12)	Temperature falling from T <sub>SD</sub>	T <sub>SDH</sub>	-	15	_	°C

11. Not characterized at  $V_{IN}$  = 3.0 V,  $V_{OUT}$  = 1.8 V,  $I_{OUT}$  = 50 mA 12. Guaranteed by design and characterization.

13. Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at  $T_J = T_A = 25^{\circ}$ C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible. 14. Respect SOA.

#### ELECTRICAL CHARACTERISTICS – Voltage Version 2.5 V

 $-40^{\circ}C \le T_J \le 125^{\circ}C$ ;  $V_{IN} = 3.5 \text{ V}$ ;  $I_{OUT} = 1 \text{ mA}$ ,  $C_{IN} = C_{OUT} = 1.0 \mu$ F, unless otherwise noted. Typical values are at  $T_J = +25^{\circ}C$ . (Note 17)

Parameter	Test Conditions	Test Conditions		Min	Тур	Max	Unit
Operating Input Voltage	0 < I <sub>OUT</sub> < 50 mA	l l	V <sub>IN</sub>	3.5		24	V
Output Voltage Accuracy	3.5 V < V <sub>IN</sub> < 24 V, 0 < I <sub>OU</sub> -	<sub>T</sub> < 50 mA	V <sub>OUT</sub>	2.45	2.5	2.55	V
Line Regulation	$V_{OUT}$ + 1 V $\leq$ V <sub>IN</sub> $\leq$ 24 V, I <sub>O</sub>	<sub>UT</sub> = 1 mA	Reg <sub>LINE</sub>		3		mV
Load Regulation	I <sub>OUT</sub> = 0 mA to 50 n	$I_{OUT} = 0 \text{ mA to } 50 \text{ mA}$			10		mV
Dropout Voltage (Note 15)	$V_{DO} = V_{IN} - (V_{OUT(NOM)} - I_{OUT} = 50 \text{ mA}$	– 75 mV)	V <sub>DO</sub>		260	450	mV
Maximum Output Current	(Note 18)		I <sub>OUT</sub>	100		200	mA
	0 < I <sub>OUT</sub> < 50 mA, -40 < T	_ <sub>A</sub> < 85°C	I <sub>GND</sub>		3.2	4.2	μΑ
Ground Current	0 < I <sub>OUT</sub> < 50 mA, Vin =	= 24 V				5.8	μΑ
Power Supply Rejection Ratio	$\label{eq:VIN} \begin{array}{l} \text{VIN} = 3.5 \text{ V},  \text{V}_{\text{OUT}} = 2.5 \text{ V} \\ \text{VPP} = 200 \text{ mV} \text{ modulation} \\ \text{I}_{\text{OUT}} = 1 \text{ mA},  \text{C}_{\text{OUT}} = 10  \mu\text{F} \end{array}$	f = 100 kHz	PSRR		60		dB
Output Noise Voltage	V <sub>OUT</sub> = 2.5 V, I <sub>OUT</sub> = 5 f = 200 Hz to 100 kHz, C <sub>OL</sub>	i0 mA <sub>JT</sub> = 10 μF	V <sub>N</sub>		115		μV <sub>rms</sub>
Thermal Shutdown Temperature (Note 16)	Temperature increasing from	TJ = +25°C	T <sub>SD</sub>		170		°C
Thermal Shutdown Hysteresis (Note 16)	Temperature falling fror	m T <sub>SD</sub>	T <sub>SDH</sub>	-	15	-	°C

15. Characterized when V<sub>OUT</sub> falls 75 mV below the regulated voltage and only for devices with V<sub>OUT</sub> = 2.5 V.
16. Guaranteed by design and characterization.
17. Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at T<sub>J</sub> = T<sub>A</sub> = 25°C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.
18. Respect SOA.

#### ELECTRICAL CHARACTERISTICS – Voltage Version 3.0 V

 $-40^{\circ}C \le T_J \le 125^{\circ}C$ ;  $V_{IN} = 4.0 \text{ V}$ ;  $I_{OUT} = 1 \text{ mA}$ ,  $C_{IN} = C_{OUT} = 1.0 \mu$ F, unless otherwise noted. Typical values are at  $T_J = +25^{\circ}C$ . (Note 21)

Parameter	Test Conditions	Symbol	Min	Тур	Max	Unit
Operating Input Voltage	0 < I <sub>OUT</sub> < 50 mA	Vin	4.0		24	V
Output Voltage Accuracy	4.0 V < V <sub>IN</sub> < 24 V, 0< I <sub>OUT</sub> < 50 mA	Vout	2.94	3.0	3.06	V
Line Regulation	$V_{OUT}$ + 1 V $\leq$ V <sub>IN</sub> $\leq$ 24 V, I <sub>OUT</sub> = 1 mA	Reg <sub>LINE</sub>		3		mV
Load Regulation	$I_{OUT} = 0 \text{ mA to } 50 \text{ mA}$	Reg <sub>LOAD</sub>		10		mV
Dropout voltage (Note 19)	$V_{DO} = V_{IN} - (V_{OUT(NOM)} - 90 \text{ mV})$ $I_{OUT} = 50 \text{ mA}$	Vdo		250	400	mV
Maximum Output Current	(Note 22)	Ιουτ	100		200	mA
Ground current	0 < I <sub>OUT</sub> < 50 mA, -40 < T <sub>A</sub> < 85°C	Ignd		3.2	4.2	μΑ
	0 < IOUT < 50 mA, VIN = 24 V				5.8	μΑ
Power Supply Rejection Ratio	$ \begin{array}{c} V_{IN} = 4.0 \text{ V}, \ V_{OUT} = 3.0 \text{ V} \\ V_{PP} = 100 \text{ mV modulation} \\ I_{OUT} = 1 \text{ mA}, \ C_{OUT} = 10 \ \mu\text{F} \end{array} \right  f = 100 \text{ kH} $	z PSRR		60		dB
Output Noise Voltage	$V_{OUT} = 3 \text{ V}, I_{OUT} = 50 \text{ mA},$ f = 200 Hz to 100 kHz, C_{OUT} = 10 $\mu\text{F}$	VN		135		μV <sub>rms</sub>
Thermal Shutdown Temperature (Note 20)	Temperature increasing from $T_J = +25^{\circ}C$	; Tsd		170		°C
Thermal Shutdown Hysteresis (Note 20)	Temperature falling from T <sub>SD</sub>	Tsdh	-	25	-	°C

19. Characterized when Vout falls 90 mV below the regulated voltage and only for devices with Vout = 3.0 V

20. Guaranteed by design and characterization. 21. Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at  $T_J = T_A = 25^{\circ}$ C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

22. Respect SOA

### ELECTRICAL CHARACTERISTICS – Voltage Version 3.3 V

 $-40^{\circ}C \le T_J \le 125^{\circ}C$ ;  $V_{IN} = 4.3 \text{ V}$ ;  $I_{OUT} = 1 \text{ mA}$ ,  $C_{IN} = C_{OUT} = 1.0 \mu$ F, unless otherwise noted. Typical values are at  $T_J = +25^{\circ}C$ . (Note 25)

					-		
Parameter	Test Conditions		Symbol	Min	Тур	Max	Unit
Operating Input Voltage	0 < I <sub>OUT</sub> < 50 mA	0 < I <sub>OUT</sub> < 50 mA		4.3		24	V
Output Voltage Accuracy	4.3 V < V <sub>IN</sub> < 24 V, 0 < I <sub>OU</sub> -	<sub>T</sub> < 50 mA	V <sub>OUT</sub>	3.234	3.3	3.366	V
Line Regulation	$V_{OUT}$ + 1 V $\leq$ VIN $\leq$ 24 V, I <sub>O</sub>	<sub>UT</sub> = 1 mA	Reg <sub>LINE</sub>		3	10	mV
Load Regulation	I <sub>OUT</sub> = 0 mA to 50 n	I <sub>OUT</sub> = 0 mA to 50 mA			10		mV
Dropout Voltage (Note 23)	$V_{DO} = V_{IN} - (V_{OUT(NOM)} - I_{OUT} = 50 \text{ mA}$	99 mV)	V <sub>DO</sub>		230	350	mV
Maximum Output Current	(Note 26)	(Note 26)		100		200	mA
Ground Current	0 < IOUT < 50 mA, -40 < T	A < 85°C	I <sub>GND</sub>		3.2	4.2	μΑ
	0 < IOUT < 50 mA, VIN =	= 24 V				5.8	μΑ
Power Supply Rejection Ratio	$\label{eq:VIN} \begin{array}{l} V_{IN} = 4.3 \ \text{V}, \ V_{OUT} = 3.3 \ \text{V} \\ V_{PP} = 200 \ \text{mV} \ \text{modulation} \\ I_{OUT} = 1 \ \text{mA}, \ C_{OUT} = 10 \ \mu\text{F} \end{array}$	f = 100 kHz	PSRR		60		dB
Output Noise Voltage	Vout = 4.3 V, lout = 5 f = 200 Hz to 100 kHz, $C_{OL}$		V <sub>N</sub>		140		$\mu V_{\text{rms}}$
Thermal Shutdown Temperature (Note 24)	Temperature increasing from	TJ = +25°C	T <sub>SD</sub>		170		°C
Thermal Shutdown Hysteresis (Note 24)	Temperature falling from	n T <sub>SD</sub>	T <sub>SDH</sub>	-	15	-	°C

23. Characterized when VOUT falls 99 mV below the regulated voltage and only for devices with VOUT = 3.3 V.

24. Guaranteed by design and characterization. 25. Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at  $T_J = T_A = 25^{\circ}C$ . Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible. 26. Respect SOA.

### ELECTRICAL CHARACTERISTICS – Voltage Version 5.0 V

 $-40^{\circ}C \le T_J \le 125^{\circ}C$ ;  $V_{IN} = 6.0 \text{ V}$ ;  $I_{OUT} = 1 \text{ mA}$ ,  $C_{IN} = C_{OUT} = 1 \mu$ F, unless otherwise noted. Typical values are at  $T_J = +25^{\circ}C$ . (Note 29)

Parameter	Test Conditions		Symbol	Min	Тур	Max	Unit
Operating Input Voltage	0 < Iоυт < 50 mA		V <sub>IN</sub>	6.0		24	V
Output Voltage Accuracy	6.0V < VIN < 24V, 0< IOUT	< 50 mA	V <sub>OUT</sub>	4.9	5.0	5.1	V
Line Regulation	Vout + 1 V $\leq$ Vin $\leq$ 24 V, Io	ut = 1mA	Reg <sub>LINE</sub>		3	10	mV
Load Regulation	IOUT = 0 mA to 50 m	IOUT = 0 mA to 50 mA			10	30	mV
Dropout Voltage (Note 27)	$V_{DO} = V_{IN} - (V_{OUT(NOM)} - T_{OUT} = 50 \text{ mA}$	150 mV)	V <sub>DO</sub>		230	350	mV
Maximum Output Current	(Note 30)	(Note 30)		90		200	mA
Ground Current	0 < IOUT < 50 mA, -40 < T	<sub>A</sub> < 85°C	I <sub>GND</sub>		3.2	4.2	μΑ
	0 < IOUT < 50 mA, VIN =	0 < Iout < 50 mA, Vin = 24 V				5.8	μΑ
Power Supply Rejection Ratio	$\label{eq:VIN} \begin{array}{l} \text{VIN} = 6.0 \text{ V}, \text{ VOUT} = 5.0 \text{ V} \\ \text{VPP} = 200 \text{ mV} \text{ modulation} \\ \text{IOUT} = 1 \text{ mA},  C_{OUT} = 10  \mu\text{F} \end{array}$	f = 100 kHz	PSRR		56		dB
Output Noise Voltage	Vout = 5.0 V, lout = 50 f = 200 Hz to 100 kHz, C <sub>OU</sub>		V <sub>N</sub>		190		μV <sub>rms</sub>
Thermal Shutdown Temperature (Note 28)	Temperature increasing from	TJ = +25°C	T <sub>SD</sub>		170		°C
Thermal Shutdown Hysteresis (Note 28)	Temperature falling from	n T <sub>SD</sub>	T <sub>SDH</sub>	-	15	-	°C

27. Characterized when VOUT falls 150 mV below the regulated voltage and only for devices with VOUT = 5.0 V.

28. Guaranteed by design and characterization. 29. Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at  $T_J = T_A = 25^{\circ}C$ . Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible. 30. Respect SOA.

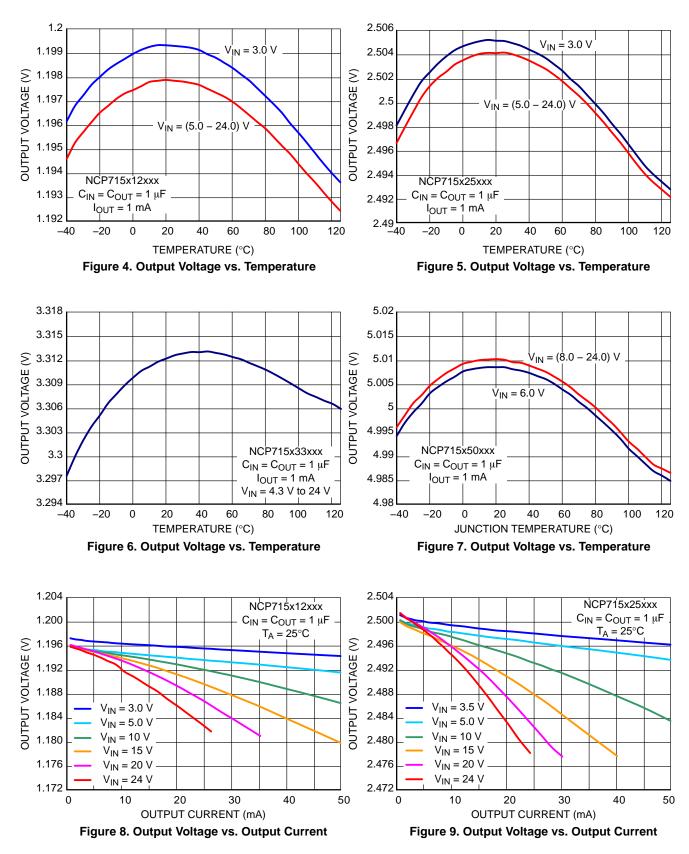
### ELECTRICAL CHARACTERISTICS – Voltage Version 5.3 V

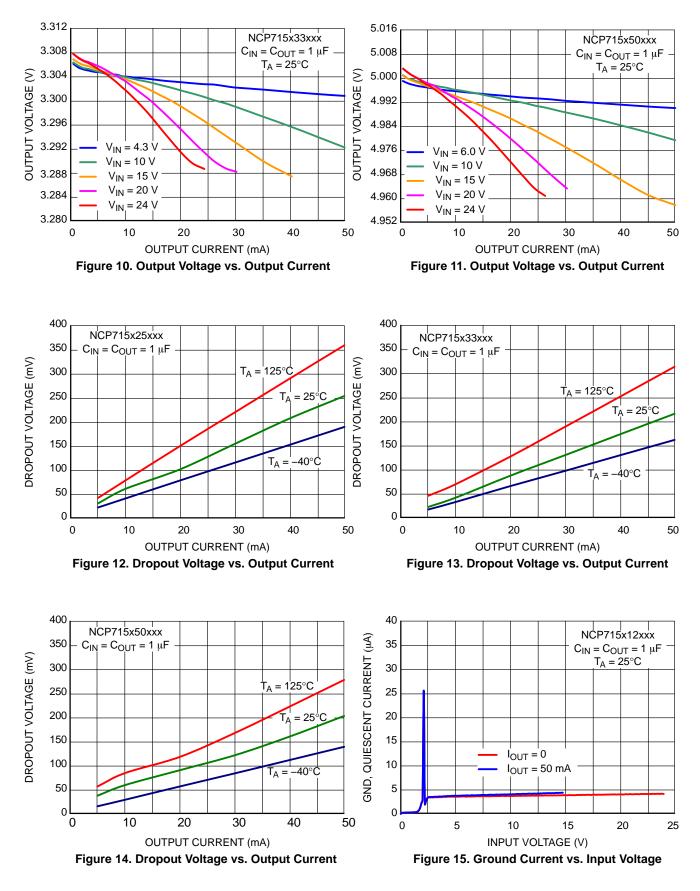
 $-40^{\circ}C \le T_J \le 125^{\circ}C$ ;  $V_{IN} = 6.3 \text{ V}$ ;  $I_{OUT} = 1 \text{ mA}$ ,  $C_{IN} = C_{OUT} = 1 \mu$ F, unless otherwise noted. Typical values are at  $T_J = +25^{\circ}C$ . (Note 33)

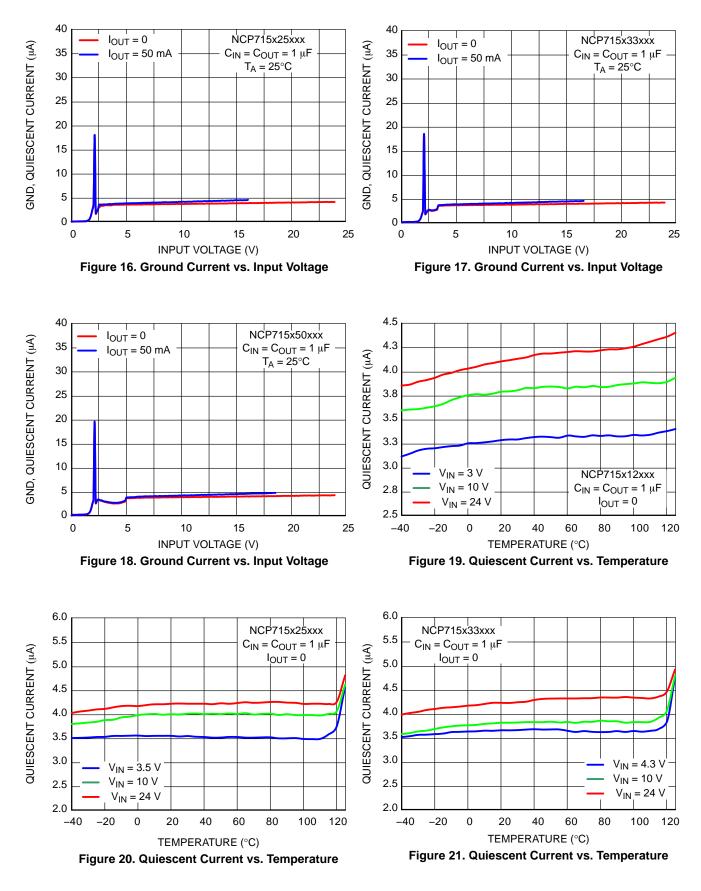
		• •		-		
Parameter	Test Conditions	Symbo	ol Min	Тур	Max	Unit
Operating Input Voltage	0 < I <sub>OUT</sub> < 50 mA	V <sub>IN</sub>	6.3		24	V
Output Voltage Accuracy	6.3V < V <sub>IN</sub> < 24V, 0.1 mA< I <sub>OUT</sub> < 5	0 mA V <sub>OUT</sub>	5.194	5.3	5.406	V
Line Regulation	$V_{OUT}$ + 1 V $\leq$ V <sub>IN</sub> $\leq$ 24 V, I <sub>OUT</sub> = 1	mA Reg <sub>LIN</sub>	E	20	60	mV
Load Regulation	I <sub>OUT</sub> = 0.1 mA to 50 mA	Reg <sub>LOA</sub>	D	20		mV
Dropout Voltage (Note 31)	$V_{DO} = V_{IN} - (V_{OUT(NOM)} - 159 \text{ m})$ $I_{OUT} = 50 \text{ mA}$	IV) V <sub>DO</sub>		230	350	mV
Maximum Output Current	(Note 34)	I <sub>OUT</sub>	90		200	mA
Ground Current	0 < I <sub>OUT</sub> < 50 mA, -40 < T <sub>A</sub> < 85	°C I <sub>GND</sub>		3.2	4.2	μΑ
	0 < I <sub>OUT</sub> < 50 mA, V <sub>IN</sub> = 24 V				5.8	μΑ
Power Supply Rejection Ratio	$ \begin{array}{c} V_{IN}=6.3 \text{ V}, V_{OUT}=5.3 \text{ V} \\ V_{PP}=200 \text{ mV modulation} \\ I_{OUT}=1 \text{ mA}, C_{OUT}=10 \ \mu F \end{array} \right  f=10 \label{eq:VIN} $	0 kHz PSRR		55		dB
Output Noise Voltage	$V_{OUT} = 5.3 \text{ V}, I_{OUT} = 50 \text{ mA}$ f = 200 Hz to 100 kHz, C <sub>OUT</sub> = 10	μF V <sub>N</sub>		195		μV <sub>rms</sub>
Thermal Shutdown Temperature (Note 32)	Temperature increasing from $T_J = -$	25°C T <sub>SD</sub>		170		°C
Thermal Shutdown Hysteresis (Note 32)	Temperature falling from T <sub>SD</sub>	T <sub>SDH</sub>	-	15	-	°C

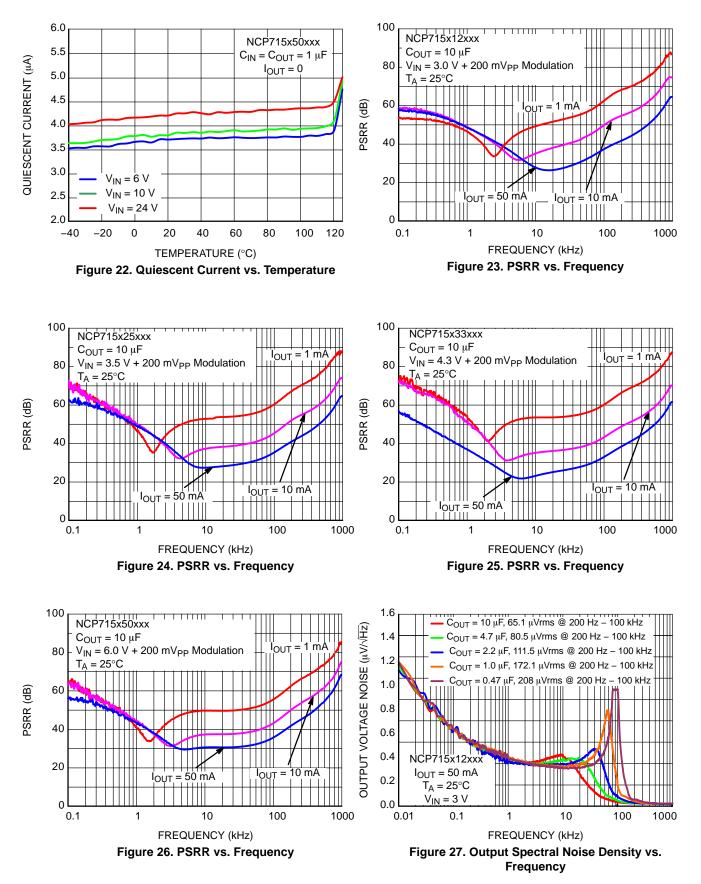
31. Characterized when Vout falls 159 mV below the regulated voltage and only for devices with Vout = 5.3 V.

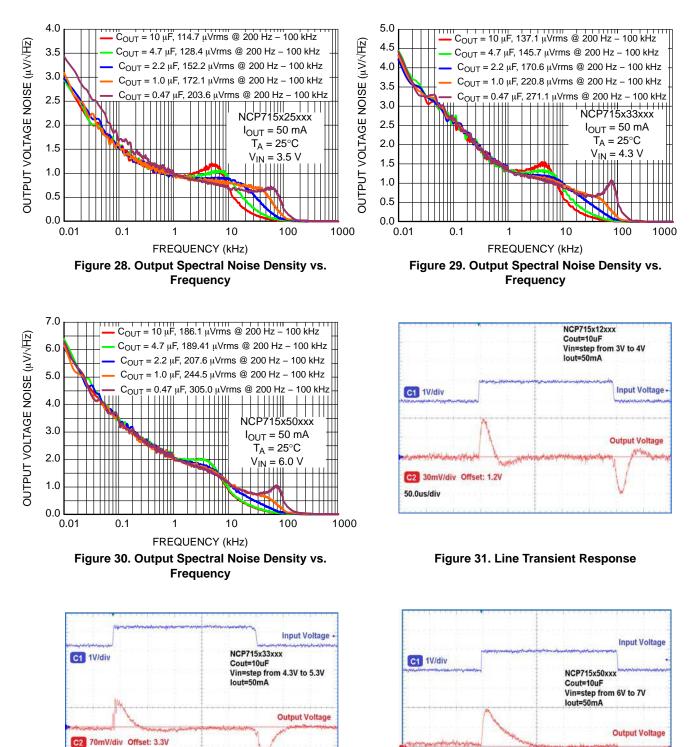
32. Guaranteed by design and characterization. 33. Performance guaranteed over the indicated operating temperature range by design and/or characterization production tested at  $T_J = T_A = 25^{\circ}$ C. Low duty cycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible. 34. Respect SOA.











<u>www.onsemi.com</u> 16

50.0us/div

Figure 32. Line Transient Response

C2 60mV/div Offset: 5.0V

Figure 33. Line Transient Response

50.0us/div

C2 100mV/div Offset: 1.2V	Output Voltage
· · · · · · · · · · · · · · · · · · ·	NCP715x12xxx Vin=3V Cout=10uF
	lout=step from 1mA to 50m/
C4 50mA/div	Output Current

Figure 34. Load Transient Response

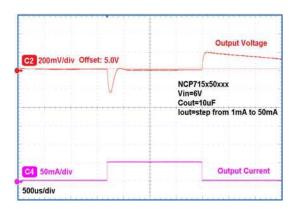


Figure 36. Load Transient Response

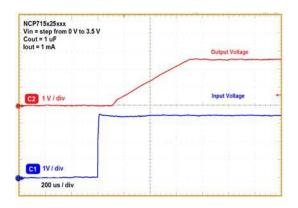


Figure 38. Input Voltage Turn-On Response

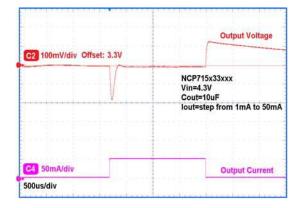


Figure 35. Load Transient Response

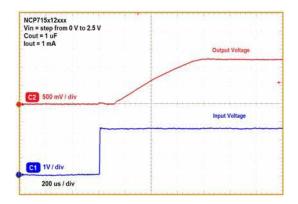


Figure 37. Input Voltage Turn-On Response

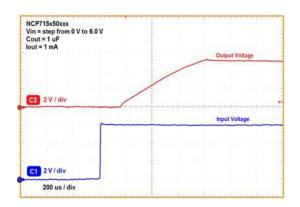


Figure 39. Input Voltage Turn-On Response

### **APPLICATIONS INFORMATION**

The NCP715 is the member of new family of Wide Input Voltage Range Low Dropout Regulators which delivers Ultra Low Ground Current consumption, Good Noise and Power Supply Rejection Ratio Performance.

#### Input Decoupling (CIN)

It is recommended to connect at least 0.1  $\mu$ F Ceramic X5R or X7R capacitor between IN and GND pin of the device. This capacitor will provide a low impedance path for any unwanted AC signals or Noise superimposed onto constant Input Voltage. The good input capacitor will limit the influence of input trace inductances and source resistance during sudden load current changes.

Higher capacitance and lower ESR Capacitors will improve the overall line transient response.

### **Output Decoupling (COUT)**

The NCP715 does not require a minimum Equivalent Series Resistance (ESR) for the output capacitor. The device is designed to be stable with standard ceramics capacitors with values of  $0.47 \,\mu\text{F}$  or greater up to  $10 \,\mu\text{F}$ . The X5R and X7R types have the lowest capacitance variations over temperature thus they are recommended.

#### Power Dissipation and Heat sinking

The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and the

#### **ORDERING INFORMATION**

ambient temperature affect the rate of junction temperature rise for the part. The maximum power dissipation the NCP715 can handle is given by:

$$\mathsf{P}_{\mathsf{D}(\mathsf{MAX})} = \frac{\left[\mathsf{T}_{\mathsf{J}(\mathsf{MAX})} - \mathsf{T}_{\mathsf{A}}\right]}{\mathsf{R}_{\mathsf{\theta}\mathsf{J}\mathsf{A}}} \tag{eq. 1}$$

The power dissipated by the NCP715 for given application conditions can be calculated from the following equations:

$$\mathsf{P}_\mathsf{D} \approx \mathsf{V}_\mathsf{IN} \big( \mathsf{I}_\mathsf{GND} \big( \mathsf{I}_\mathsf{OUT} \big) \big) + \mathsf{I}_\mathsf{OUT} \big( \mathsf{V}_\mathsf{IN} - \mathsf{V}_\mathsf{OUT} \big) \ (\text{eq. 2})$$

$$V_{\text{IN(MAX)}} \approx \frac{\mathsf{P}_{\text{D(MAX)}} + \left( V_{\text{OUT}} \times I_{\text{OUT}} \right)}{I_{\text{OUT}} + I_{\text{GND}}} \qquad (\text{eq. 3})$$

For reliable operation, junction temperature should be limited to  $+125^{\circ}$ C maximum.

#### Hints

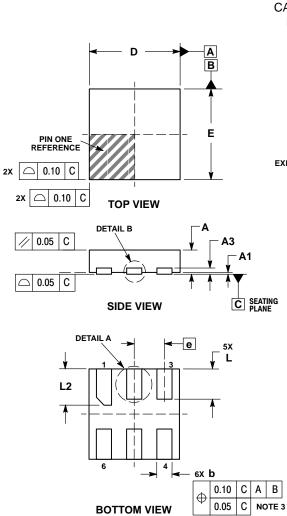
or

VIN and GND printed circuit board traces should be as wide as possible. When the impedance of these traces is high, there is a chance to pick up noise or cause the regulator to malfunction. Place external components, especially the output capacitor, as close as possible to the NCP715, and make traces as short as possible.

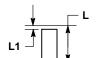
Device	Nominal Output Voltage	Marking	Marking Rotation	Package	Shipping <sup>†</sup>
NCP715SQ12T2G	1.2 V	5A		SC88A/SC70 (Pb–Free)	3000 / Tape & Reel
NCP715SQ15T2G	1.5 V	5C			
NCP715SQ18T2G	1.8 V	5D			
NCP715SQ25T2G	2.5 V	5E			
NCP715SQ30T2G	3.0 V	5F			
NCP715SQ33T2G	3.3 V	5G			
NCP715SQ50T2G	5.0 V	5H			
NCP715MX12TBG	1.2 V	Q	0°	XDFN6 1.5 x 1.5 (Pb–Free)	
NCP715MX15TBG	1.5 V	R			
NCP715MX18TBG	1.8 V	Т			
NCP715MX25TBG	2.5 V	V			
NCP715MX30TBG	3.0 V	Y			
NCP715MX33TBG	3.3 V	2			
NCP715MX50TBG	5.0 V	5			
NCP715MX53TBG	5.3 V	5	+180°		

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

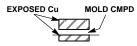
### PACKAGE DIMENSIONS



XDFN6 1.5x1.5, 0.5P CASE 711AE **ISSUE B** 

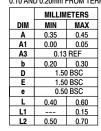


DETAIL A ALTERNATE TERMINAL CONSTRUCTIONS

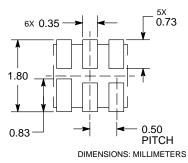


DETAIL B ALTERNATE CONSTRUCTIONS NOTES: 1. DIMENSIONING AND TOLERANCING PER

ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.



#### RECOMMENDED **MOUNTING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE L

NOTES:

3. 4

BURRS

DIM

A B

С

D

G

н

J

κ

Ν

 $\frac{0.65}{0.025}$ 

<u>0.65</u> 0.025

mm

SCALE 20:1

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.

419A–01 OBSOLETE. NEW STANDARD 419A–02.

INCHES

MIN MAX

0.071 0.087

0.045 0.053

0.031 0.043

0.004 0.012

0.026 BSC

0.004 0.010

0.004 0.012

0.008 REF

S 0.079 0.087

0.004

DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE

MILLIMETERS

MIN MAX

2.20

1.35

1.10

0.30

0.10

0.25

1.80

1.15

0.80

0.10

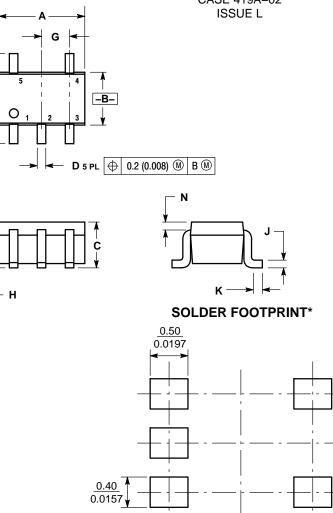
0.10

0.65 BSC

0.10 0.30

2.00 2.20

0.20 REF



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

<u>1.9</u> 0.0748

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns me rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor ."Typical" parameters which may be provided in ON Semiconductor date sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights or others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor hardles, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or un

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

s

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative